MCC1536 MCC1436

Advance Information

HIGH VOLTAGE, INTERNALLY COMPENSATED MONOLITHIC OPERATIONAL AMPLIFIER CHIP

 \dots designed for use as a summing amplifier, integrator, or amplifier with operating characteristics as a function of the external feedback components.

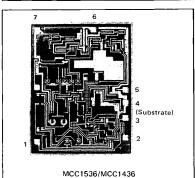
The MCC1536 and MCC1436 employ phosphorsilicate passivation that protects the entire die surface area, including metalization interconnects. All dice have a minimum gold-backed thickness of 4000 Angstroms. The interconnecting metalization and bonding pads are of evaporated aluminum.

- Maximum Supply Voltage − ± 40 Vdc
- Output Voltage Swing
 - $\pm 30 \text{ V}_{pk(min)}(V^{+} = +36 \text{ V}, V^{-} = -36 \text{ V})$
 - $\pm 22 \text{ Vpk(min)}(V^{+} = +28 \text{ V}, V^{-} = -28 \text{ V})$
- Input Bias Current 20 nA max
- Input Offset Current − 3.0 nA max Offset Voltage Null Capability
- Fast Slew Rate 2.0 V/μs typ
- Internally Compensated
- Input Over-Voltage Protection
- AVOL 500,000 typ
- Characteristics Independent of Power Supply Voltages (±5.0 Vdc to ±36 Vdc)

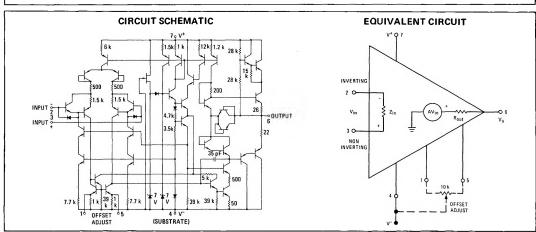
MAYIMINA DATINGS (T. = ±250C uplass otherwise noted)

OPERATIONAL AMPLIFIER CHIP MONOLITHIC SILICON INTEGRATED CIRCUIT

EPITAXIAL PASSIVATED



Rating	Symbol	MCC1536	MCC1436	Unit Vdc	
Power Supply Voltage	v+	+40	+34		
	v-	-40	-34		
Differential Input Signal (1)	V _{in}	±(V* +	Volts		
Common-Mode Input Swing	CMVin	+V ⁺ , -(V ⁻ -3)		Volts	
Output Short Circuit Duration ($V^+ = V^- = 28 \text{ Vdc}, V_0 = 0$)	T _{SC}	5	s		
Operating Temperature Range	TA	-55 to	°c		
Junction Temperature Range	T _{stg}	-65 to	°c		



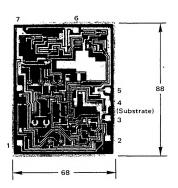
This is advance information and specifications are subject to change without notice.

ELECTRICAL CHARACTERISTICS (V⁺ = +28 Vdc, V⁻ = -28 Vdc, T_A = +25°C unless otherwise noted)

Characteristics		MCC1536			MCC1436			
	Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Input Bias Current	1 _b	-	8.0	20	-	15	40	nAdc
Input Offset Current	I _{io}	-	1.0	3.0	-	5.0	10	nAdc
Input Offset Voltage	Iviol	-	2.0	5.0	-	5.0	10	mVdc
Differential Input Impedance (Open-Loop, f ≤ 5.0 Hz) Parallel Input Resistance Parallel Input Capacitance	Я _р С _р	1 1	10 2.0		-	10 2.0		Meg ahm pF
Common-Mode Input Impedance (f ≤ 5.0 Hz)	Z _(in)	-	250	-	-	250		Meg ohm
Common-Mode Input Voltage Swing	CMVin	-	±25	-	<u> </u>	±25	-	Vpk
Common-Mode Rejection Ratio (dc)	CM _{rej}	-	110	-	-	110	-	dB
Large Signal dc Open Loop Voltage Gain	AVOL							V/V
(V _O = ± 10 V, R _L = 100 k ohms)		100,000	500,000	-	70,000	500,000	-	
$(V_0 = \pm 10 \text{ V}, R_L = 10 \text{ k ohms})$		_	200,000	-	-	200,000	-	
Power Bandwidth (Voltage Follower) $(A_V = 1, R_L = 5.0 \text{ k ohms}, THD \le 5\%, V_O = 40 \text{ Vp-p})$	PBW	-	23	_	_	23	_	kHz
Unity Gain Crossover Frequency (open-loop)			1.0		-	1.0	_	MHz
Phase Margin (open-loop, unity gain)			50	0-0	<u> </u>	50	-	degrees
Gain Margin		_	18	_	_	18	_	dB
Slew Rate (Unity Gain)	dV _{out} /dt	_	2.0	-	_	2.0	_	V/µs
Output Impedance (f ≤ 5.0 Hz)	Zout	_	1.0			1.0	_	k ohms
Short-Circuit Output Current	¹sc	_	±17	_		±17	_	mAdc
Output Voltage Swing (R _L = 5.0 k ohms) V ⁺ = +28 Vdc, V ⁻ = -28 Vdc V ⁺ = +36 Vdc, V ⁻ = -36 Vdc	v _o	±22 ±30	±23 ±32	-	±20 -	±22 -	-	V _{pk}
Power Supply Sensitivity (dc) $V^- = constant, \ R_S \le 10 \ k \ ohms$ $V^+ = constant, \ R_S \le 10 \ k \ ohms$	S+ S-	-	15 15	100	-	35 35	200 200	μV/V
Power Supply Current	1D-	- 6	2.2 2.2	4.0 4.0	-	2.6 2.6	5.0 5.0	mAdc
DC Quiescent Power Dissipation (Vo = 0)	PD	-	124	224	3	146	280	mW

See current MC1536/1436 data sheet for additional information.

MCC1536/MCC1436 BONDING DIAGRAM



PACKAGING AND HANDLING

The MCC1536/MCC1436 operational amplifier is now available in die (chip) form. The phosphorsilicate passivation protects the metalization and active area of the die but care must be exercized when removing the dice from the shipping carrier to avoid scratching the bonding pads. A vacuum pickup is useful for the handling of dice. Tweezers are not recommended for this purpose.

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The non-spill type shipping carrier consists of a compartmentalized tray and fitted cover. Die are placed in the carrier with geometry side up.

All dimensions are nominal and in mils (10⁻³ inches). Die Dimensions
Thickness = 8.0
Bonding Pads = 4.0 × 4.0